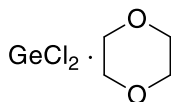


Catalog # 32-3215 Germanium(II) chloride dioxane adduct



Thermal Behavior:

- Melting point: 176-178°C [1]

Technical Notes:

- ALD/CVD precursor for Ge thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
GeT	ALD	60-70°C	7.5 Torr, 2.25 Torr	(Et ₃ Si) ₂ Te	90-175°C	2-5
Ge ₂ Sb ₂ Te ₅	ALD	70°C	7.5 Torr	(Et ₃ Si) ₂ Te, SbCl ₃	90°C	6
GeSb	ALD	70°C	-	Sb(SiEt ₃) ₃	100°C	7
GeSe	ALD	70-90°C	-	(Me ₃ Si) ₂ Se, (Et ₃ Si) ₂ Se	100-150°C	8

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